

BC303**BC304**

PNP SILICON AF MEDIUM POWER AMPLIFIERS & SWITCHES

CASE TO-39

THE BC303, BC304 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS RECOMMENDED FOR AF DRIVERS & OUTPUTS, AS WELL AS FOR SWITCHING APPLICATIONS UP TO 1 AMPERE. THEY ARE COMPLEMENTARY TO THE NPN TYPE BC300, BC301, BC302.

**ABSOLUTE MAXIMUM RATINGS**

		BC303	BC304
Collector-Base Voltage	-V _{CB0}	85V	60V
Collector-Emitter Voltage	-V _{CEO}	60V	45V
Emitter-Base Voltage	-V _{EB0}	7V	7V
Collector Current	-I _C	1A	
Total Power Dissipation (T _C ≤ 25°C)	P _{tot}	6W	
		850mW	
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to 175°C	

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	-V _{CEO} *					-I _C =100mA I _B =0
BC303		60			V	
BC304		45			V	
Collector-Emitter Breakdown Voltage	-V _{CEV}					-I _C =100mA -V _{EB} =1.5V
BC303 only		85			V	
Collector Cutoff Current	-I _{CB0}			20	nA	-V _{CB} =60V I _E =0
Emitter Cutoff Current	-I _{EB0}			20	nA	-V _{EB} =5V I _C =0
Collector-Emitter Saturation Voltage	-V _{CE(sat)} *		0.1	0.65	V	-I _C =150mA -I _B =15mA
Base-Emitter Voltage	-V _{BE} *		0.78		V	-I _C =150mA -V _{CE} =10V
D.C. Current Gain	H _{FE} *	20				-I _C =0.1mA -V _{CE} =10V
		40		240		-I _C =150mA -V _{CE} =10V
		20				-I _C =500mA -V _{CE} =10V
D.C. Current Gain	H _{FE} *	40		80		-I _C =150mA -V _{CE} =10V
Group 4		70		140		
Group 5		120		240		
Group 6						
Current Gain-Bandwidth Product	f _T		100		MHz	-I _C =10mA -V _{CE} =10V
Collector-Base Capacitance	C _{ob}		17		pF	-V _{CB} =10V I _E =0 f=1MHz

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%

MICRO ELECTRONICS LTD.

38 HUNG TO ROAD, KWUN TONG, HONG KONG. TELEX 43510
 KWUN TONG P. O. BOX 69477 CABLE ADDRESS "MICROTRON"
 TELEPHONE:- 3-430181-6 3-893363, 3-892423
 FAX: 3-410321

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TYPICAL CHARACTERISTICS

